## Electronics II

## Frequency analysis

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1)

A certain commercial amplifier has the following parameters

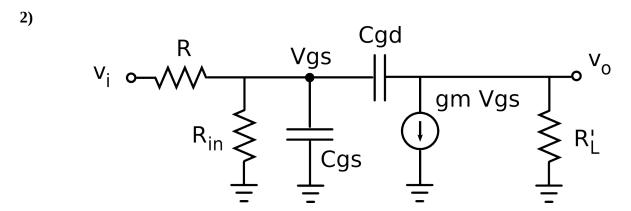
- Voltage gain: A = -100 V/V.
- Input resistance:  $r_{\rm in} = 5 \text{ k}\Omega$ .
- Output resistance:  $r_{\text{out}} = 1 \text{ k}\Omega$ .
- Capacitance between the input and output:  $C_f = 10 \text{ pF}$ .
- Capacitance between the input and the box (ground) and the output and the box (ground):  $C_i = C_o = 10 \text{ pF}$ .

Based on this amplifier the following circuit was designed

$$v_i \dots \xrightarrow{R_S} C_S$$
 $C_S$ 
 $C_S$ 
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$$R_{\rm S} = 1 \text{ k}\Omega, R_{\rm L} = 3 \text{ k}\Omega, C_{\rm S} = C_{\rm L} = 10 \text{ }\mu\text{F}.$$

- a) Determine the mid-frequency gain of the complete circuit.
- b) Schematically draw Bode plots of the behavior of the circuit in terms of frequency.
- c) Determine the band-width of the circuit.



The figure above shows an equivalent circuit of an common-source FET amplifier. The input signal comes from a signal generator with an output resistance R.  $R_{\rm in}$  represents the input resistance of the FET stage and is caused by the gate-bias resistances.  $R_{\rm L}$ ' is the parallel equivalent resistance composed

of load  $R_L$ , drain resistance  $R_D$  and FET output resistance  $r_o$ . Capacitors  $C_{gs}$  and  $C_{gd}$  are internal capacitors of the FET.

 $R = 100 \text{ k}\Omega$ ,  $R_{\text{in}} = 420 \text{ k}\Omega$ ,  $C_{\text{gs}} = C_{\text{gd}} = 1 \text{ pF}$ ,  $g_{\text{m}} = 4 \text{ mA/V}$ ,  $R_{\text{L}}' = 3.33 \text{ k}\Omega$ .

- a) Determine the mid-band gain,  $A_v = v_0/v_i$ .
- b) Determine the bandwidth of the circuit.